

In the claims:

Please substitute the following full listing of claims for the claims as originally filed or most recently amended.

1. (Currently amended) A field effect transistor formed at a surface of a layer of semiconductor material, said field effect transistor comprising
  - a gate structure formed on said surface of said layer of semiconductor material, and
  - a discontinuous film of material within said layer of semiconductor material and having a discontinuity formed in alignment with aligned to said gate structure.
2. (Currently amended) A field effect transistor as recited in claim 1, wherein said discontinuity is self-aligned with to said gate structure.
3. (Original) A field effect transistor as recited in claim 1, wherein said discontinuous film is a stressed film
4. (Original) A field effect transistor as recited in claim 3, wherein said stressed film comprises an insulator.
5. (Original) A field effect transistor as recited in claim 1, wherein said discontinuous film comprises an insulator.
6. (Original) A field effect transistor as recited in claim 1, wherein said discontinuous film has a stepped or staircase profile in cross-section.
7. (Original) A field effect transistor as recited in claim 3, wherein said stressed film has a stepped or staircase profile in cross-section.
8. (Original) A field effect transistor as recited in claim 7 wherein said stepped or staircase portion defines an effective channel depth.
9. (Original) A field effect transistor as recited in claim 1, wherein said discontinuous film is an insulator including a portion formed of oxidized SiGe, wherein said

discontinuity defines a location of a conductor connected to a channel of said field effect transistor.

10. (Original) A field effect transistor as recited in claim 1, further including a void within said layer of semiconductor material.

11. (Currently amended) An integrated circuit including a field effect transistor formed at a surface of a layer of semiconductor material, said field effect transistor comprising

a gate structure formed on said surface of said layer of semiconductor material, and

a discontinuous film of material within said layer of semiconductor material and having a discontinuity formed in alignment with aligned to said gate structure.

12. (Original) An integrated circuit as recited in claim 11, wherein said discontinuous film has a stepped or staircase profile in cross-section.

13. (Previously presented) An integrated circuit as recited in claim 12 wherein said stepped or staircase portion defines an effective channel depth.

14. (Original) An integrated circuit as recited in claim 11, wherein said discontinuous film is an insulator including a portion formed of oxidized SiGe, wherein said discontinuity defines a location of a conductor connected to a channel of said field effect transistor.

15. (Original) An integrated circuit as recited in claim 11, further including a void within said layer of semiconductor material.

16. - 20 (Canceled)

21. (Previously presented) A field effect transistor formed at a surface of a layer of semiconductor material, said field effect transistor comprising

a gate structure formed on said surface of said layer of semiconductor material, and

a discontinuous film of material within said layer of semiconductor material at a predetermined distance from said surface of said layer of semiconductor material, said discontinuous film having a discontinuity which includes an edge which is located in a position defined by an edge said gate structure,

said discontinuity defining a structure for performing at least one of:

defining a depth of a conduction channel of said field effect transistor within said layer of semiconductor material to less than said predetermined distance from said surface of said semiconductor material; and

applying stress to said conduction channel of said field effect transistor.

22. (Currently amended) A field effect transistor as recited in claim 21, wherein said discontinuity is self-aligned ~~with~~ to said gate structure.

23. (Previously presented) A field effect transistor as recited in claim 21, wherein said discontinuous film is a stressed film

24. (Previously presented) A field effect transistor as recited in claim 23, wherein said stressed film comprises an insulator.

25. (Previously presented) A field effect transistor as recited in claim 21, wherein said discontinuous film comprises an insulator.